





SN65MLVD047A JAJSTH2B - JULY 2006 - REVISED MARCH 2024

# SN65MLVD047A マルチポイント LVDS クワッド差動ライン ドライバ

# 1 特長

- 30Ω~55Ω の負荷とデータ レート用の差動ラインドラ イバ <sup>1</sup> 最大 200Mbps、最大 100MHz のクロック周波
- マルチポイント バス アーキテクチャをサポート
- 3.3V 単一電源で動作
- -40℃~85℃ の温度範囲で動作を規定
- 16ピン SOIC (JEDEC MS-012) および 16ピン TSSOP (JEDEC MS-153) パッケージ

# 2 アプリケーション

- AdvancedTCA™ (ATCA™) クロック バスドライバ
- クロック分配
- テレコミュニケーション、車載用、産業用、その他のコン ピュータシステムにおける、バックプレーンまたはケー ブルによるマルチポイントデータ伝送
- 携帯基地局
- 本および PBX スイッチング
- ブリッジおよびルータ
- 低消費電力、高速、短距離での TIA / EIA-485 の代

## 3 概要

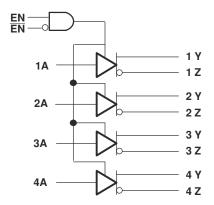
SN65MLVD047A は、TIA/EIA-899 規格、マルチポイント 低電圧差動信号処理 (M-LVDS) の電気的特性に準拠し たクワッド ライン ドライバです。この M-LVDS デバイスの 出力電流は、二重終端の伝送ラインと高負荷のバックプレ ーン バス アプリケーションに対応するため、標準の LVDS 準拠デバイスに比べて増加しています。 バックプレーン ア プリケーションでは一般に、バスの両端でインピーダンス 整合の終端抵抗が必要です。二重終端バスの実効インピ ーダンスは、バス終端とバス インターフェイス デバイスの 容量性負荷により、30Ω まで下げることができます。 SN65MLVD047A ドライバにより、最小 30Ω の負荷での 動作が可能です。SN65MLVD047A デバイスは、単一の バス上に複数のドライバを存在させることができます。 SN65MLVD047A ドライバは、ディセーブルまたは電源オ フ時に高インピーダンスになります。動作をサポートするた め、ドライバのエッジレート制御が組み込まれています。 M-LVDS 規格では、メイン伝送ラインからインターフェイス デバイスへの複数のバススタブが予想される場合、最大 32 ノード (ドライバまたはレシーバ) をバックプレーン内の 同じメディアに接続できます。SN65MLVD047Aは、すべ てのバスピンに 9kV ESD 保護を実現します。

#### パッケージ情報

部品番号	パッケージ <sup>(1)</sup>	パッケージ サイズ <sup>(2)</sup>
SN65MLVD047A	PW (TSSOP, 16)	5mm × 6.4mm
	D (SOIC, 16)	9.9mm × 6mm

- 詳細は、セクション 11 を参照してください。 (1)
- パッケージ サイズ (長さ×幅) は公称値であり、該当する場合はピ ンも含まれます。

### LOGIC DIAGRAM (POSITIVE LOGIC)



1 ラインのデータレートは 1 秒あたりの電圧遷移回数で、bps (Bits Per Second) 単位で表されます。



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# **4 Pin Configuration**

D PACKAGE (TOP VIEW)			PW PACKAGE (TOP VIEW)		
EN III 1A III 2A III VCC III GND III	10 10 2 11 3 14 4 13 5 13	1 1Y 1 2Y 3 2 2Z 2 3Z	VCC GND	10 16 2 15 3 14 4 13 5 12	1Z 1Y 2Y 2Z 3Z
3A —— 4A —— EN ——	6 1 7 10 8	·	4A 🞞	6 11 7 10 8 9	3Y 4Y 4Z

3

Product Folder Links: SN65MLVD047A



## **5 Specifications**

## 5.1 Absolute Maximum Ratings

over operating free-air temperature range unless otherwise noted<sup>(1)</sup>

			MIN	MAX	UNITS
V <sub>CC</sub>	Supply voltage range <sup>(2)</sup>		-0.5	4	V
VI	Input voltage range	A, EN, EN	-0.5	4	V
Vo	Output voltage range	Y, Z	-1.8	4	V
TJ	Junction temperature			140	°C
P <sub>D</sub>	Device power dissipation	$EN = V_{CC}$ , $\overline{EN} = GND$ , $R_L = 50Ω$ , Input 100MHz 50 % duty cycle square wave to 1A:4A, $T_A = 85$ °C		288.5	mW
T <sub>stg</sub>	Storage Temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

All voltage values, except differential I/O bus voltages, are with respect to the circuit ground terminal.

## 5.2 ESD Ratings

				VALUE	UNIT
V <sub>(ESD)</sub> Electrostatic discha		Human body model (HBM), per ANSI/ ESDA/JEDEC JS-001 <sup>(1)</sup>	Y and Z	±9000	
			All pins	±4000	
	Electrostatic discharge	Charged device model (CDM), per AEC Q100-011 <sup>(2)</sup>	All pins	±1500	V
		Machine Model	All pins	±200	

JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.

## 5.3 Recommended Operating Conditions

#### see 🗵 6-1

		MIN	NOM	MAX	UNIT
V <sub>CC</sub>	Supply voltage	3	3.3	3.6	V
V <sub>IH</sub>	High-level input voltage	2		V <sub>CC</sub>	V
V <sub>IL</sub>	Low-level input voltage	0		0.8	V
	Voltage at any bus terminal (separate or common mode) V <sub>Y</sub> or V <sub>Z</sub>	-1.4		3.8	V
$R_L$	Differential load resistance	30		55	Ω
1/t <sub>UI</sub>	Signaling rate			200	Mbps
	Clock frequency			100	MHz
TJ	Junction temperature	-40		125	°C

## 5.4 Package Dissipation Ratings

PACKAGE	PCB JEDEC STANDARD	T <sub>A</sub> ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C <sup>(1)</sup>	T <sub>A</sub> = 85°C POWER RATING
D(16)	Low-K <sup>(2)</sup>	898mW	7.81mW/°C	429mW
D\\/(16)	Low-K <sup>(2)</sup>	592mW	5.15mW/°C	283mw
PW(16)	High-K <sup>(3)</sup>	945mW	8.22mW/°C	452mw

Product Folder Links: SN65MLVD047A

- This is the inverse of the junction-to-ambient thermal resistance when board mounted and with no air flow.
- (2) In accordance with the Low-K thermal metric definitions of EIA/JESD51-3.
- In accordance with the High-K thermal metric definitions of EIA/JESD51-7. (3)

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JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.



## 5.5 Thermal Information

PARAMETER		TEST CONDITIONS		VALUE	UNIT
		Low-K board <sup>(1)</sup> , no airflow	D	128	
		Low-K board <sup>(1)</sup> , no airflow		194.2	
$\theta_{JA}$	Junction-to-ambient thermal resistance	Low-K board <sup>(1)</sup> , 150 LFM	PW	146.8	°C/W
		Low-K board <sup>(1)</sup> , 250 LFM	PVV	133.1	
		High-K board <sup>(2)</sup> , no airflow		121.6	
Δ	Junction-to-board thermal resistance	High-K board <sup>(2)</sup>	D	51.1	°C/W
$\theta_{JB}$	Junction-to-poard thermal resistance		PW	85.3	C/VV
$\theta_{JC}$	Junction-to-case thermal resistance		D	45.4	°C/W
	Junction-to-case thermal resistance		PW	34.7	C/VV

<sup>(1)</sup> In accordance with the Low-K thermal metric definitions of EIA/JESD51-3.

### 5.6 Device Electrical Characteristics

over recommended operating conditions unless otherwise noted

	PARAMETER		TEST CONDITIONS		TYP <sup>(1)</sup>	MAX	UNIT
I <sub>CC</sub> Supply current	Driver enabled	EN = $V_{CC}$ , $\overline{EN}$ = GND, $R_L$ = 50 $\Omega$ , All inputs = $V_{CC}$ or GND		59	70	mA	
	Driver disabled	$EN = GND$ , $\overline{EN} = V_{CC}$ , $R_L = No load$ , $All inputs = V_{CC}$ or $GND$		2	4	ША	

<sup>(1)</sup> All typical values are at 25°C and with a 3.3V supply voltage.

<sup>(2)</sup> In accordance with the High-K thermal metric definitions of EIA/JESD51-7.



#### 5.7 Device Electrical Characteristics

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN <sup>(1)</sup>	TYP <sup>(2)</sup> MA	X UNIT
LVTTL (E	N, <u>EN</u> , 1A:4A)				'
I <sub>IH</sub>	High-level input current	V <sub>IH</sub> = 2 V or V <sub>CC</sub>	0	1	0 μΑ
I <sub>IL</sub>	Low-level input current	V <sub>IL</sub> = GND or 0.8 V	0	1	0 μΑ
Ci	Input capacitance	$V_1 = 0.4 \sin(30E6\pi t) + 0.5 V^{(3)}$		5	pF
M-LVDS (	1Y/1Z:4Y/4Z)				
$ V_{YZ} $	Differential output voltage magnitude		480	65	0 mV
$\Delta  V_{YZ} $	Change in differential output voltage magnitude between logic states	See 図 6-2	-50	Ę	0 mV
V <sub>OS(SS)</sub>	Steady-state common-mode output voltage		0.8	1	2 V
$\Delta V_{OS(SS)}$	Change in steady-state common-mode output voltage between logic states	See 図 6-3	-50	Ę	0 mV
V <sub>OS(PP)</sub>	Peak-to-peak common-mode output voltage			15	0 mV
V <sub>Y(OC)</sub>	Maximum steady-state open-circuit output voltage	0	0	2	4 V
V <sub>Z(OC)</sub>	Maximum steady-state open-circuit output voltage	-See ⊠ 6-7	0	2	4 V
V <sub>P(H)</sub>	Voltage overshoot, low-to-high level output	0		1.2 V <sub>3</sub>	s V
$V_{P(L)}$	Voltage overshoot, high-to-low level output	- See 図 6-5	-0.2 V <sub>SS</sub>		V
I <sub>OS</sub>	Differential short-circuit output current magnitude	See 図 6-4		2	4 mA
I <sub>OZ</sub>	High-impedance state output current	$-1.4 \text{ V} \le (\text{V}_{\text{Y}} \text{ or } \text{V}_{\text{Z}}) \le 3.8 \text{ V},$ Other output = 1.2 V	-15	1	0 μΑ
I <sub>O(OFF)</sub>	Power-off output current	$-1.4 \text{ V} \le (\text{V}_{\text{Y}} \text{ or } \text{V}_{\text{Z}}) \le 3.8 \text{ V},$ Other output = 1.2 V, $\text{V}_{\text{CC}} = 0 \text{ V}$	-10	1	0 μΑ
C <sub>Y</sub> or C <sub>Z</sub>	Output capacitance	$V_Y$ or $V_Z$ = 0.4 sin(30E6 $\pi$ t) + 0.5 V, <sup>(3)</sup> Other input at 1.2 V, driver disabled		3	pF
C <sub>YZ</sub>	Differential output capacitance	V <sub>YZ</sub> = 0.4 sin(30E6πt) V, <sup>(3)</sup> Driver disabled		2	5 pF
C <sub>Y/Z</sub>	Output capacitance balance, (C <sub>Y</sub> /C <sub>Z</sub> )		0.99	1.01	

The algebraic convention, in which the least positive (most negative) limit is designated as minimum is used in this data sheet. (1)

All typical values are at 25°C and with a 3.3-V supply voltage. HP4194A impedance analyzer (or equivalent) (2)

<sup>(3)</sup> 



## 5.8 Switching Characteristics

over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
t <sub>PLH</sub>	Propagation delay time, low-to-high-level output		1	1.5	2.4	ns
t <sub>PHL</sub>	Propagation delay time, high-to-low-level output		1	1.5	2.4	ns
t <sub>r</sub>	Differential output signal rise time		1		1.9	ns
t <sub>f</sub>	Differential output signal fall time	See ⊠ 6-5	1		1.9	ns
t <sub>sk(o)</sub>	Output skew <sup>(2)</sup>				100	ps
t <sub>sk(p)</sub>	Pulse skew ( t <sub>pHL</sub> - t <sub>pLH</sub>  )			22	100	ps
t <sub>sk(pp)</sub>	Part-to-part skew <sup>(3)</sup>				600	ps
t <sub>jit(per)</sub>	Period jitter, rms (1 standard deviation) <sup>(4)</sup>	All inputs 100 MHz clock input		0.2	1	ps
t <sub>jit(c-c)</sub>	Cycle-to-cycle jitter <sup>(4)</sup>	All inputs 100 MHz clock input		5	36	ps
t <sub>jit(pp)</sub>	Peak-to-peak jitter <sup>(4) (5)</sup>	All inputs 200 Mbps 2 <sup>15</sup> -1 PRBS input		46	158	ps
t <sub>PZH</sub>	Enable time, high-impedance-to-high-level output	C W C C			9	ns
t <sub>PZL</sub>	Enable time, high-impedance-to-low-level output	- See 図 6-6			9	ns
t <sub>PHZ</sub>	Disable time, high-level-to-high-impedance output	C W C C			10	ns
t <sub>PLZ</sub>	Disable time, low-level-to-high-impedance output	─See 図 6-6			10	ns

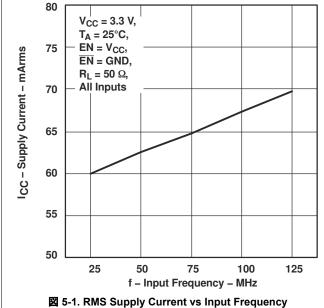
- (1) All typical values are at 25°C and with a 3.3V supply voltage.
- (2)  $t_{sk(o)}$ , output skew is the magnitude of the time difference in propagation delay times between any specified terminals of a device.
- (3)  $t_{sk(pp)}$  is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.
- (4) Stimulus jitter has been subtracted from the measurements.
- (5) Peak-to-peak jitter includes jitter due to pulse skew (t<sub>sk(p)</sub>).

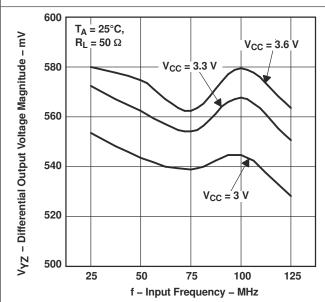
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## 5.9 Typical Characteristics





☑ 5-3. Differential Output Voltage Magnitude vs Input Frequency

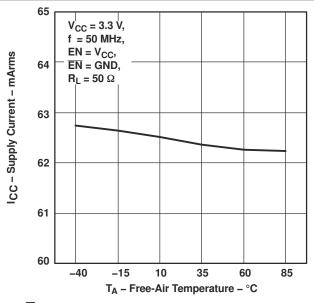
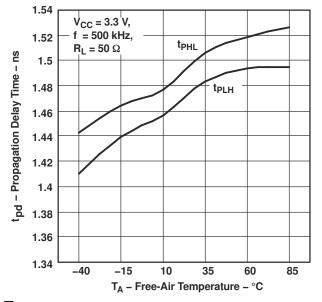


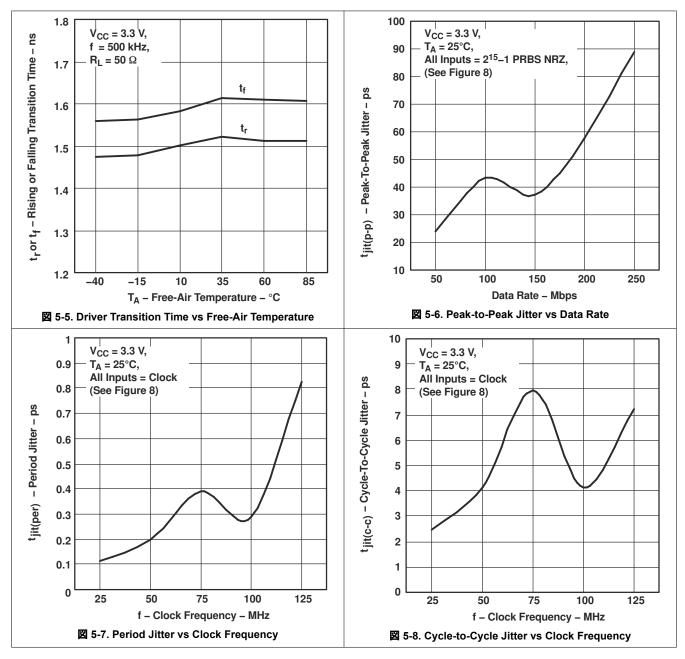
図 5-2. RMS Supply Current vs Free-Air Temperature



☑ 5-4. Driver Propagation Delay Time vs Free-Air Temperature

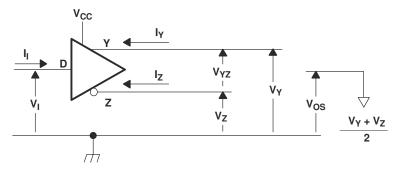


# **5.9 Typical Characteristics (continued)**

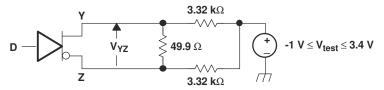




## **6 Parameter Measurement Information**

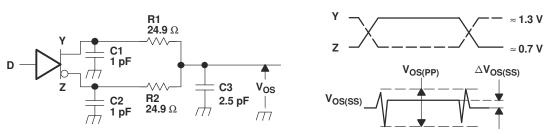


**図** 6-1. Driver Voltage and Current Definitions



All resistors are 1% tolerance.

## 図 6-2. Differential Output Voltage Test Circuit



- All input pulses are supplied by a generator having the following characteristics: t<sub>r</sub> or t<sub>f</sub> ≤ 1ns, pulse frequency = 500kHz, duty cycle = 50 ± 5%.
- B. C1, C2 and C3 include instrumentation and fixture capacitance within 2 cm of the D.U.T. and are ±20%.
- C. R1 and R2 are metal film, surface mount, ±1%, and located within 2 cm of the D.U.T.
- D. The measurement of V<sub>OS(PP)</sub> is made on test equipment with a –3dB bandwidth of at least 1 GHz.

## 図 6-3. Test Circuit and Definitions for the Common-Mode Output Voltage

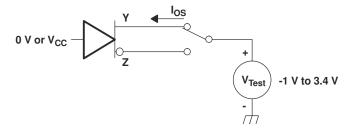
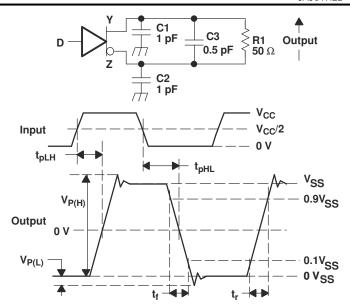
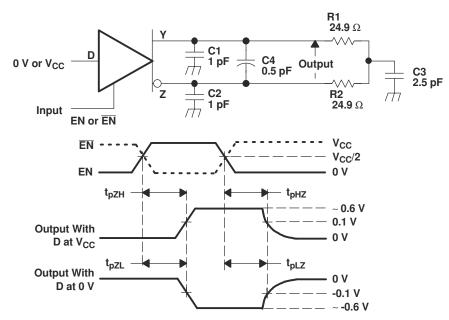


図 6-4. Short-Circuit Test Circuit



- A. All input pulses are supplied by a generator having the following characteristics: t<sub>r</sub> or t<sub>f</sub> ≤ 1ns, frequency = 500kHz, duty cycle = 50 ± 5%.
- B. C1, C2, and C3 include instrumentation and fixture capacitance within 2 cm of the D.U.T. and are ±20%.
- C. R1 is a metal film, surface mount, and 1% tolerance and located within 2 cm of the D.U.T.
- D. The measurement is made on test equipment with a –3dB bandwidth of at least 1 GHz.

## 図 6-5. Driver Test Circuit, Timing, and Voltage Definitions for the Differential Output Signal



- A. All input pulses are supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 1$ ns, frequency = 500kHz, duty cycle = 50 ± 5%
- B. C1, C2, C3, and C4 includes instrumentation and fixture capacitance within 2 cm of the D.U.T. and are ±20%.
- C. R1 and R2 are metal film, surface mount, and 1% tolerance and located within 2 cm of the D.U.T.
- D. The measurement is made on test equipment with a -3dB bandwidth of at least 1GHz.

#### 図 6-6. Driver Enable and Disable Time Circuit and Definitions



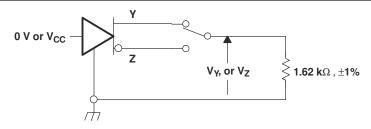
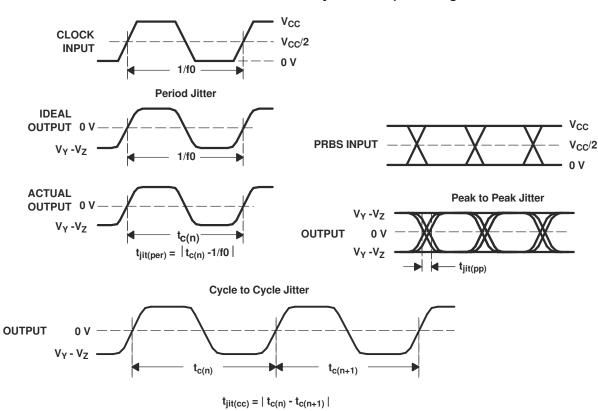


図 6-7. Driver Maximum Steady State Output Voltage



- A. All input pulses are supplied by an Agilent 8304A Stimulus System.
- B. The measurement is made on a TEK TDS6604 running TDSJIT3 application software
- C. Period jitter and cycle-to-cycle jitter are measured using a 100MHz 50 ±1% duty cycle clock input.
- D. Peak-to-peak jitter is measured using a 200Mbps 2<sup>15</sup> 1PRBS input.

図 6-8. Driver Jitter Measurement Waveforms



# 7 Device Functional Modes

表 7-1. Device Function Table

INPUTS <sup>(1)</sup>			OUTPUTS <sup>(1)</sup>		
D	EN	EN	Y	Z	
L	Н	L	L	Н	
Н	Н	L	Н	L	
OPEN	Н	L	L	Н	
X	L or OPEN	X	Z	Z	
X	X	H or OPEN	Z	Z	

(1) H = high level, L = low level, Z = high impedance, X = Don't Care

DRIVER INPUT AND ACTIVE-HIGH ENABLE

DRIVER OUTPUT

**ACTIVE-LOW ENABLE** 

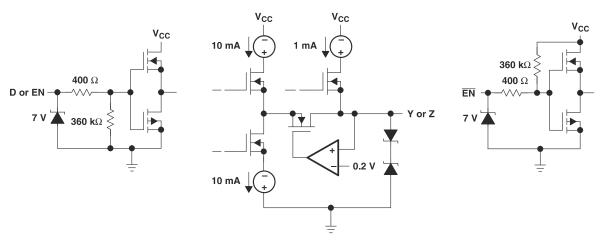


図 7-1. Equivalent Input and Output Schematic Diagrams

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Product Folder Links: SN65MLVD047A

# 8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

## 8.1 Application Information

### 8.1.1 Synchroization Clock in AdvancedTCA

Advanced Telecommunications Computing Architecture, also known as AdvancedTCA, is an open architecture to meet the needs of the rapidly changing communications network infrastructure. M-LVDS bused clocking is recommended by the ATCA.

The ATCA specification includes requirements for three redundant clock signals. An 8KHz and a 19.44MHz clock signal as well as an user-defined clock signal are included in the specification. The SN65MLVD047A guad driver supports distribution of these three ATCA clock signals, supporting operation beyond 100MHz, which is the highest clock frequency included in the ATCA specification. A pair of SN65MLVD047A devices can be used to support the ATCA redundancy requirements.

#### 8.1.2 Multipoint Configuration

The SN65MLVD047A is designed to meet or exceed the requirement of the TIA/EIA-899 (M-LVDS) standard, which allows multipoint communication on a shared bus.

Multipoint is a bus configuration with multiple drivers and receivers present. An example is shown in 🗵 8-1. The figure shows transceivers interfacing to the bus, but a combination of drivers, receivers, and transceivers is also possible. Termination resistors need to be placed on each end of the bus, with the termination resistor value matched to the loaded bus impedance.

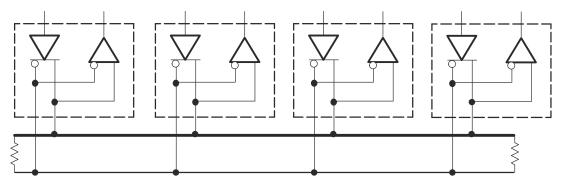


図 8-1. Multipoint Architecture

Product Folder Links: SN65MLVD047A English Data Sheet: SLLS736

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#### 8.1.3 Multidrop Configuration

Multidrop configuration is similar to multipoint configuration, but only one driver is present on the bus. A multidrop system can be configured with the driver at one end of the bus, or in the middle of the bus. When a driver is located at one end, a single termination resistor is located at the far end, close to the last receiver on the bus. Alternatively, the driver can be located in the middle of the bus, to reduce the maximum flight time. With a centrally located driver, termination resistors are located at each end of the bus. In both cases, the termination resistor value should be matched to the loaded bus impedance.  $\boxtimes$  8-2 shows examples of both cases.

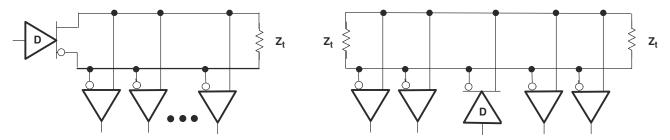


図 8-2. Multidrop Architectures With Different Driver Locations

#### 8.1.4 Unused Channel

A 360k $\Omega$  pull-down resistor is built in every LVTTL input. The unused driver inputs should be left floating or connected to ground. The low-level output of an unused enabled driver can oscillate if left floating, and should be connected to ground. If the input is floating or connected to ground, the unused Y (non-inverting) output of an enabled driver should be connected to ground. The unused Z (inverting) should be left floating



## 9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

## 9.1 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。 変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

## 9.2 サポート・リソース

テキサス・インスツルメンツ E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計で必要な支援を迅速に得ることができます。

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## 9.3 Trademarks

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## 9.4 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

## 9.5 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。

## 10 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

## Changes from Revision A (July 2005) to Revision B (February 2024)

Page

### 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

資料に関するフィードバック(ご意見やお問い合わせ)を送信

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#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN65MLVD047AD	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD047A	Samples
SN65MLVD047ADG4	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD047A	Samples
SN65MLVD047ADR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MLVD047A	Samples
SN65MLVD047APW	ACTIVE	TSSOP	PW	16	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BUL	Samples
SN65MLVD047APWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	BUL	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



# PACKAGE OPTION ADDENDUM

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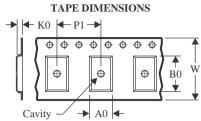
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

# **PACKAGE MATERIALS INFORMATION**

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## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65MLVD047ADR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN65MLVD047APWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

# **PACKAGE MATERIALS INFORMATION**

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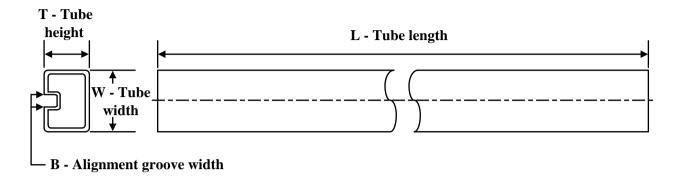
## \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins SPQ		Length (mm)	Width (mm)	Height (mm)	
SN65MLVD047ADR	SOIC	D	16	2500	350.0	350.0	43.0	
SN65MLVD047APWR	TSSOP	PW	16	2000	350.0	350.0	43.0	

# **PACKAGE MATERIALS INFORMATION**

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## **TUBE**



\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN65MLVD047AD	D	SOIC	16	40	505.46	6.76	3810	4
SN65MLVD047ADG4	D	SOIC	16	40	505.46	6.76	3810	4
SN65MLVD047APW	PW	TSSOP	16	90	530	10.2	3600	3.5

# D (R-PDS0-G16)

# PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.





SMALL OUTLINE PACKAGE



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



## 重要なお知らせと免責事項

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